

N-channel 25 V, 0.01 Ω , 40 A, DPAK, IPAK
STripFET™ V Power MOSFET

Features

Type	V_{DSS}	$R_{DS(on)}$ max	I_D
STD40N2LH5	25 V	0.0118 Ω	40 A
STU40N2LH5	25 V	0.0124 Ω	40 A

- $R_{DS(on)} * Q_g$ industry benchmark
- Extremely low on-resistance $R_{DS(on)}$
- Very low switching gate charge
- High avalanche ruggedness
- Low gate drive power losses

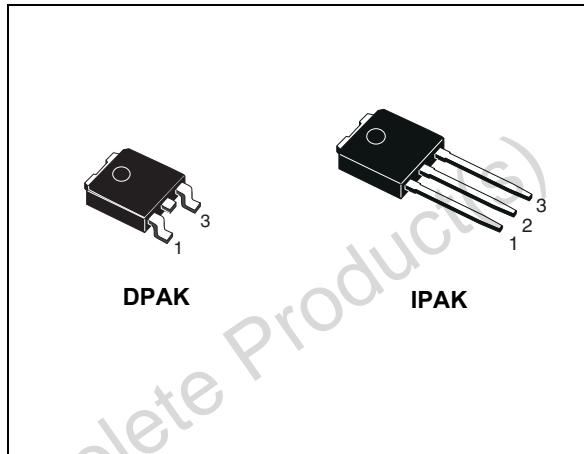


Figure 1. Internal schematic diagram

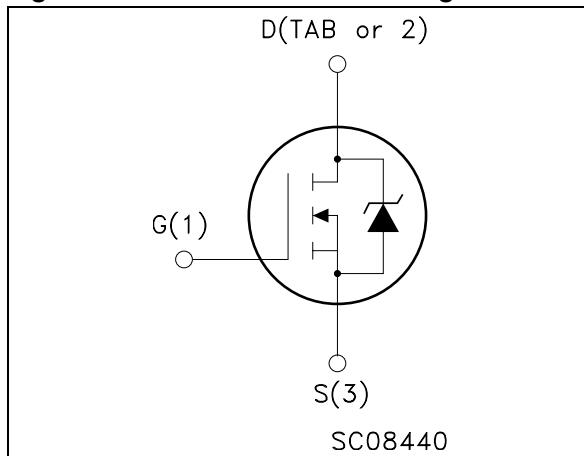


Table 1. Device summary

Order codes	Marking	Package	Packaging
STD40N2LH5	40N2LH5	DPAK	Tape and reel
STU40N2LH5	40N2LH5	IPAK	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS}=0$)	25	V
V_{GS}	Gate-Source voltage	± 22	V
I_D	Drain current (continuous) at $T_C = 25^\circ\text{C}$	40	A
I_D	Drain current (continuous) at $T_C = 100^\circ\text{C}$	28	A
$I_{DM}^{(1)}$	Drain current (pulsed)	160	A
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	35	W
	Derating factor	0.23	W/ $^\circ\text{C}$
$E_{AS}^{(2)}$	Single pulse avalanche energy	110	mJ
T_j T_{stg}	Operating junction temperature Storage temperature	-55 to 175	$^\circ\text{C}$

1. Pulse width limited by safe operating area
2. Starting $T_j = 25^\circ\text{C}$, $I_D = 24 \text{ A}$, $V_{DD} = 12 \text{ V}$

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	4.3	$^\circ\text{C/W}$
$R_{thj-amb}$	Thermal resistance junction-case max	100	$^\circ\text{C/W}$
T_L	Maximum lead temperature for soldering purpose	275	$^\circ\text{C}$

2 Electrical characteristics

($T_{CASE} = 25^\circ\text{C}$ unless otherwise specified)

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250 \mu\text{A}, V_{GS} = 0$	25			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 25 \text{ V}$ $V_{DS} = 25 \text{ V}, T_C = 125^\circ\text{C}$			1 10	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 22 \text{ V}$			± 100	nA
$V_{GS(\text{th})}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	1			V
$R_{DS(\text{on})}$	Static drain-source on resistance	$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$ SMD version		0.01	0.0118	Ω
		$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$		0.0106	0.0124	Ω
		$V_{GS} = 5 \text{ V}, I_D = 20 \text{ A}$ SMD version		0.0135	0.0155	Ω
		$V_{GS} = 5 \text{ V}, I_D = 20 \text{ A}$		0.0141	0.0161	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance			700		pF
C_{oss}	Output capacitance	$V_{DS} = 20 \text{ V}, f = 1 \text{ MHz}$, $V_{GS} = 0$	-	160	-	pF
C_{rss}	Reverse transfer capacitance			27		pF
Q_g	Total gate charge	$V_{DD} = 15 \text{ V}, I_D = 40 \text{ A}$		6.3		nC
Q_{gs}	Gate-source charge	$V_{GS} = 5 \text{ V}$	-	2.4	-	nC
Q_{gd}	Gate-drain charge	(Figure 14)		2.7		nC

Table 6. Switching on/off (resistive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(\text{on})}$ t_r	Turn-on delay time Rise time	$V_{DD} = 10 \text{ V}, I_D = 20 \text{ A}$, $R_G = 4.7 \Omega, V_{GS} = 10 \text{ V}$ (Figure 13 and Figure 18)	-	4.8 13.6	-	ns ns
$t_{d(\text{off})}$ t_f	Turn-off delay time Fall time	$V_{DD} = 10 \text{ V}, I_D = 20 \text{ A}$, $R_G = 4.7 \Omega, V_{GS} = 10 \text{ V}$ (Figure 13 and Figure 18)	-	17.6 3.5	-	ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		40	A
I_{SDM}	Source-drain current (pulsed) ⁽¹⁾				160	A
V_{SD}	Forward on voltage	$I_{SD} = 20 \text{ A}, V_{GS}=0$	-		1.1	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 40 \text{ A},$ $di/dt = 100 \text{ A}/\mu\text{s},$ $V_{DD} = 20 \text{ V}, T_j = 25 \text{ }^\circ\text{C}$ (Figure 15)	-	17.6 9.2 1		ns nC A

1. Pulsed: pulse duration = 300μs, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

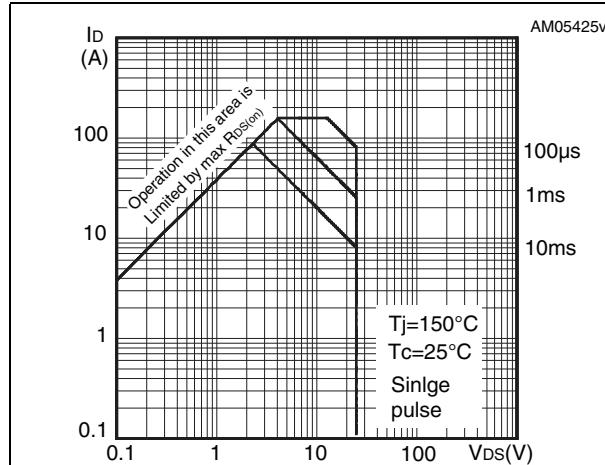


Figure 3. Thermal impedance

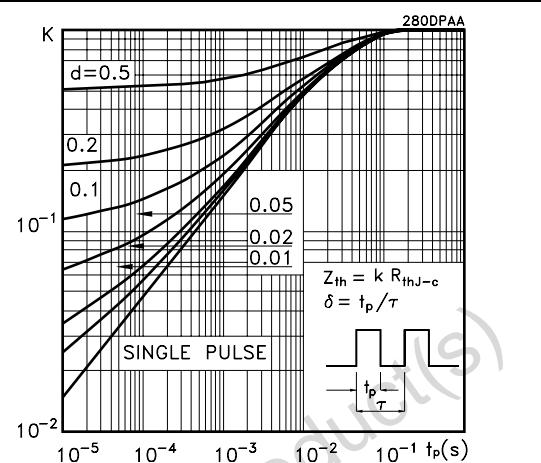


Figure 4. Output characteristics

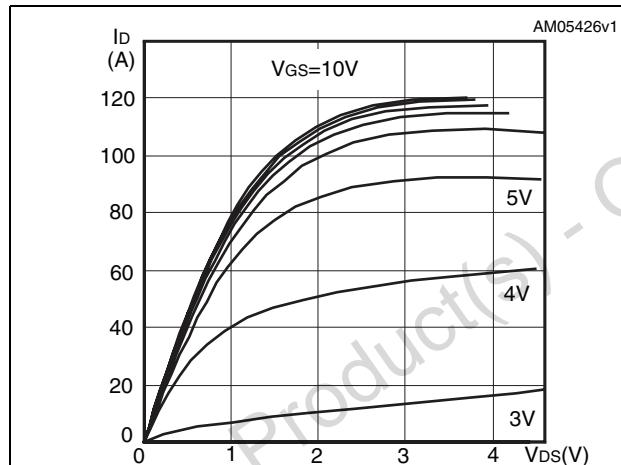


Figure 5. Transfer characteristics

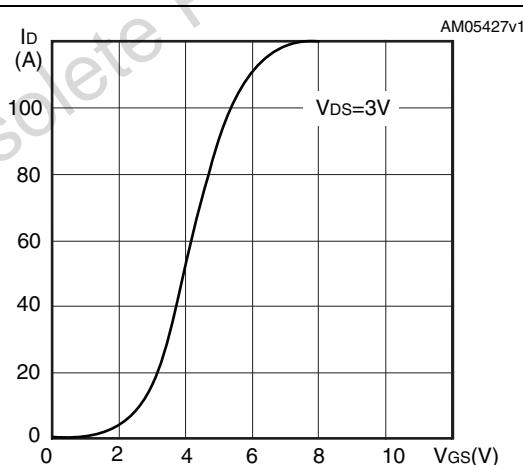
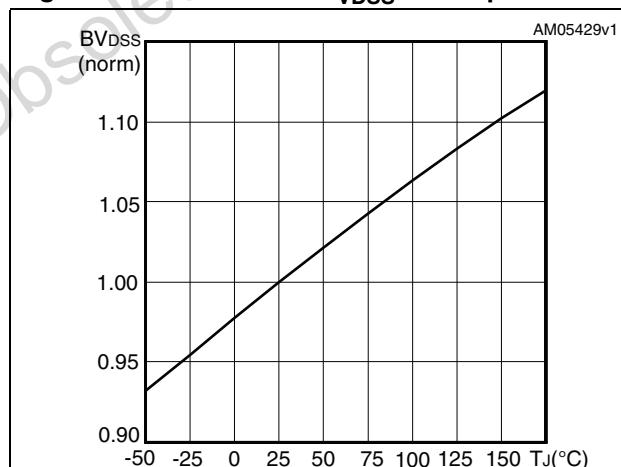
Figure 6. Normalized B_{VDSS} vs temperature

Figure 7. Static drain-source on resistance

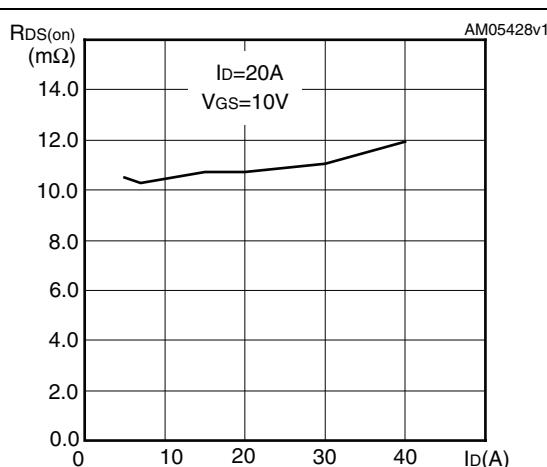
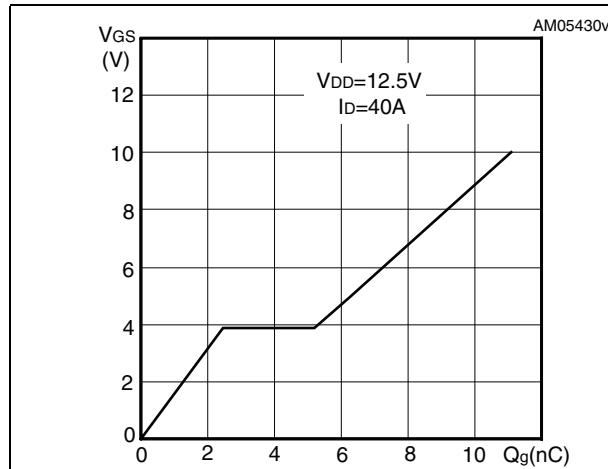
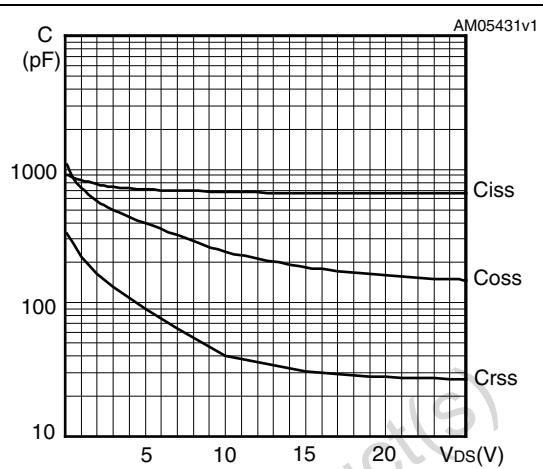
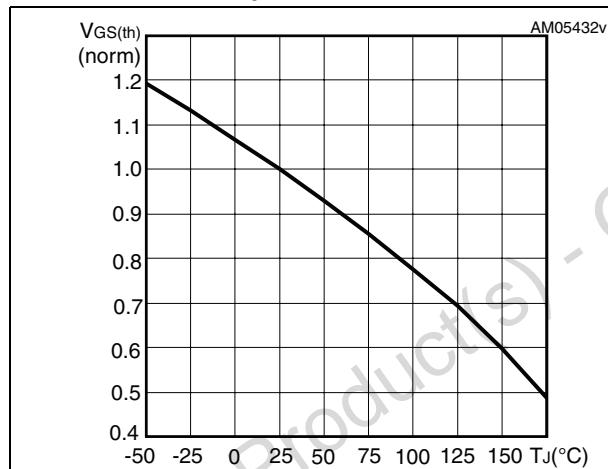
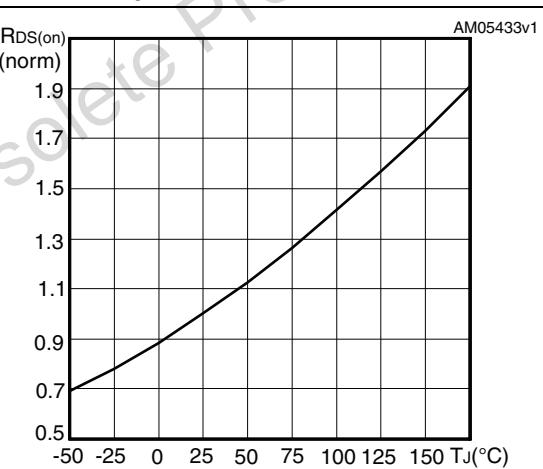
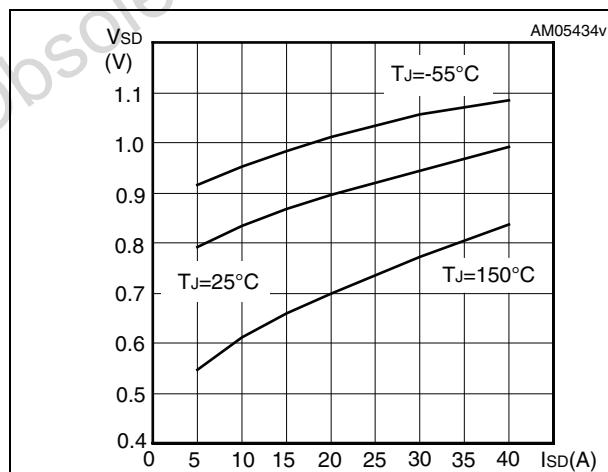


Figure 8. Gate charge vs gate-source voltage**Figure 9. Capacitance variations****Figure 10. Normalized gate threshold voltage vs temperature****Figure 11. Normalized on resistance vs temperature****Figure 12. Source-drain diode forward characteristics**

3 Test circuits

Figure 13. Switching times test circuit for resistive load

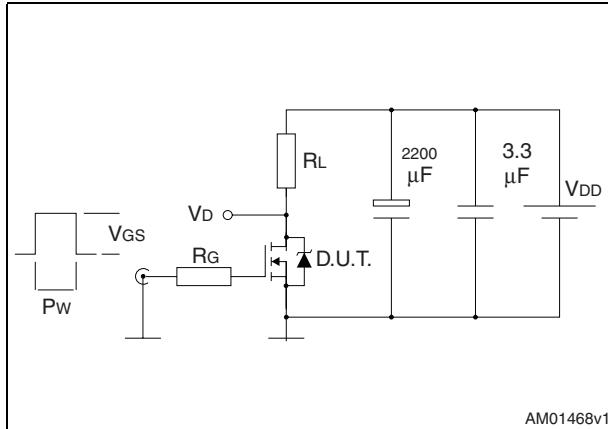


Figure 14. Gate charge test circuit

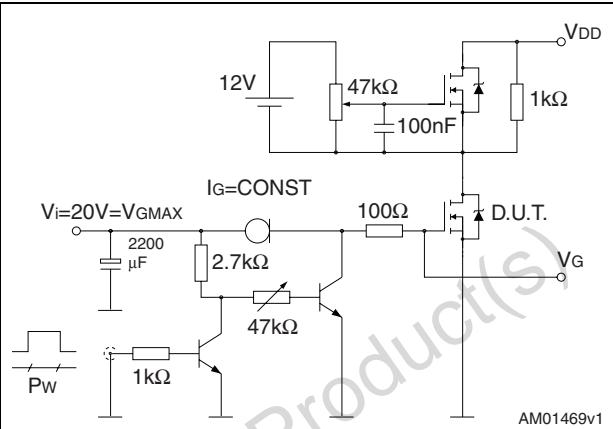


Figure 15. Test circuit for inductive load switching and diode recovery times

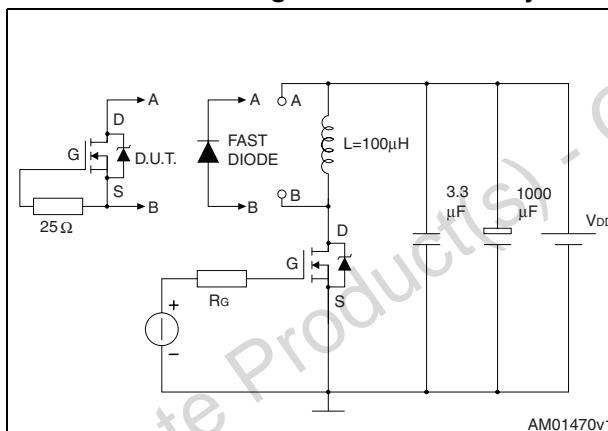


Figure 16. Unclamped Inductive load test circuit

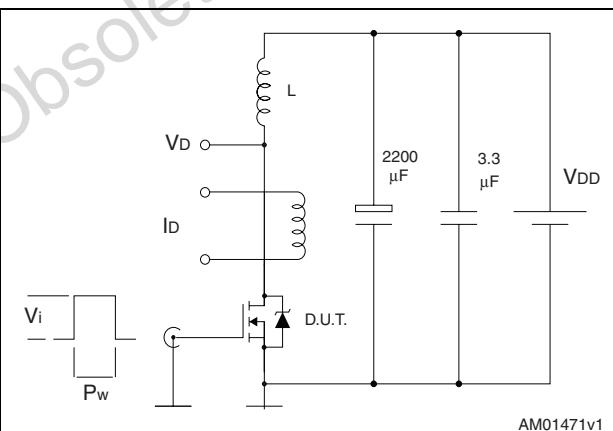


Figure 17. Unclamped inductive waveform

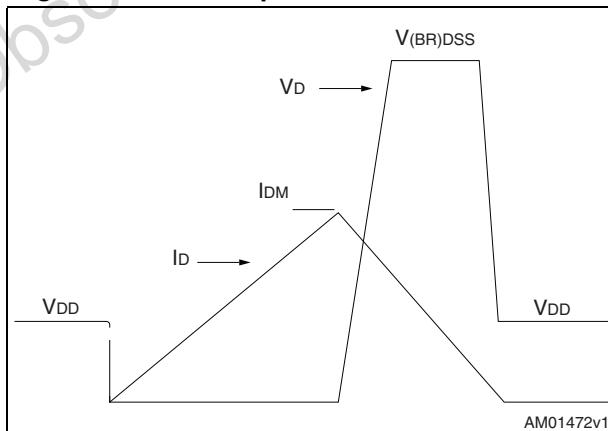


Figure 18. Switching time waveform

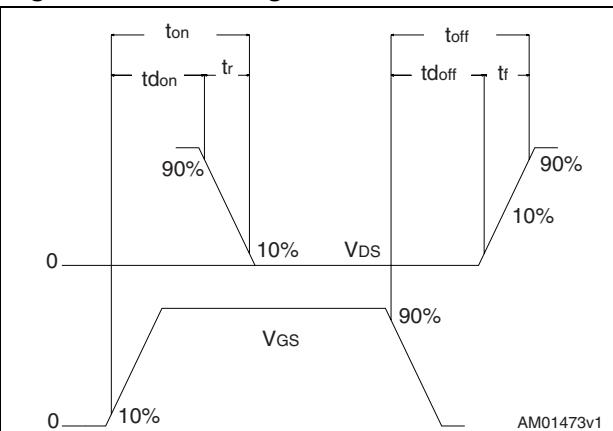
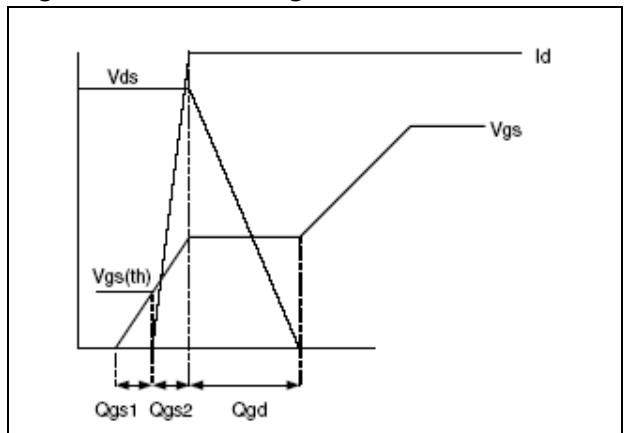


Figure 19. Gate charge waveform

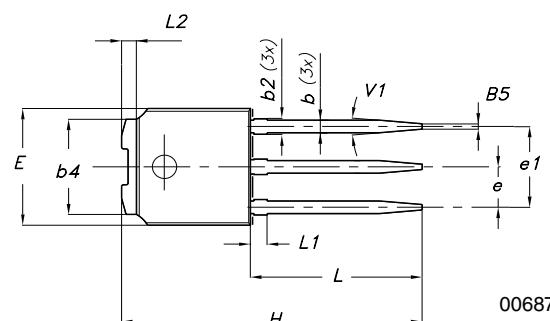
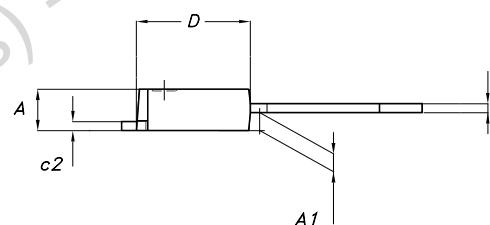
4 Package mechanical data

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Obsolete Product(s) - Obsolete Product(s)

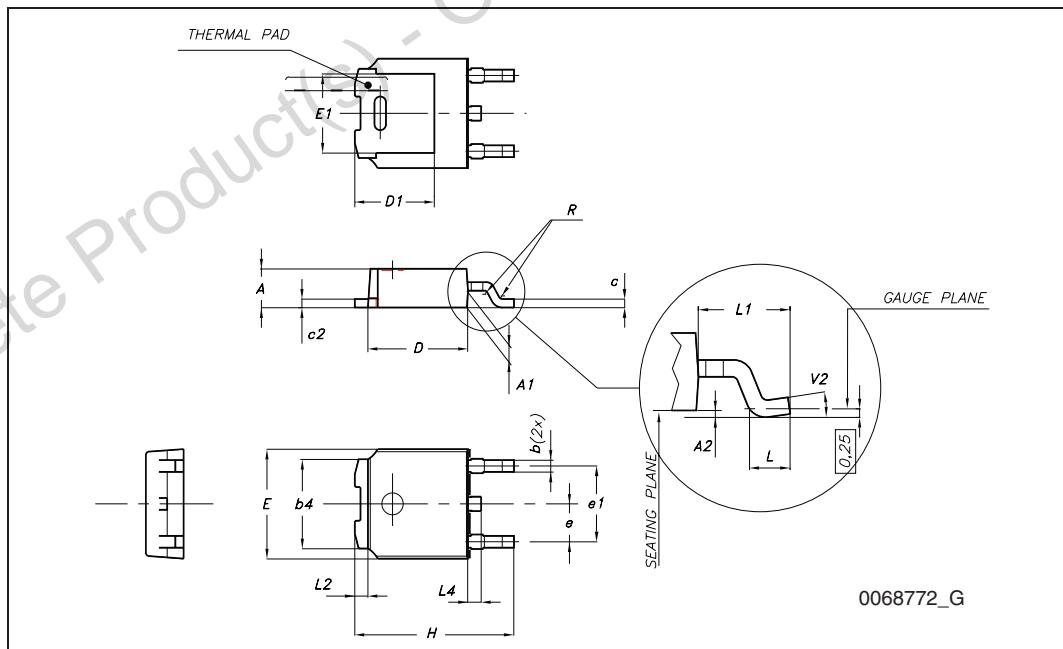
TO-251 (IPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
(L1)	0.80		1.20
L2		0.80	
V1		10°	



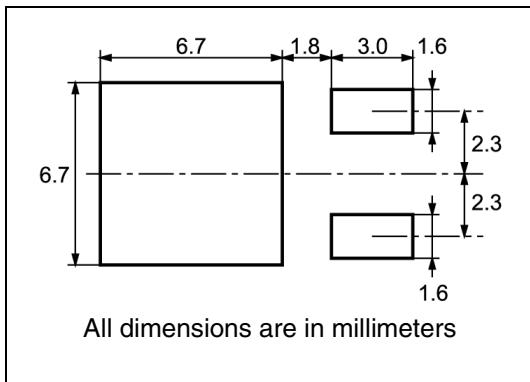
TO-252 (DPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0 °		8 °



5 Packaging mechanical data

DPAK FOOTPRINT



TAPE AND REEL SHIPMENT

REEL MECHANICAL DATA				
DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

BASE QTY	BULK QTY
2500	2500

TAPE MECHANICAL DATA				
DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A ₀	6.8	7	0.267	0.275
B ₀	10.4	10.6	0.409	0.417
B ₁		12.1		0.476
D	1.5	1.6	0.059	0.063
D ₁	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K ₀	2.55	2.75	0.100	0.108
P ₀	3.9	4.1	0.153	0.161
P ₁	7.9	8.1	0.311	0.319
P ₂	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641

6 Revision history

Table 8. Document revision history

Date	Revision	Changes
24-Jul-2008	1	Initial release
23-Sep-2008	2	V_{GS} value has been changed on Table 2 and Table 5
10-Sep-2009	3	Document status promoted from preliminary data to datasheet.

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